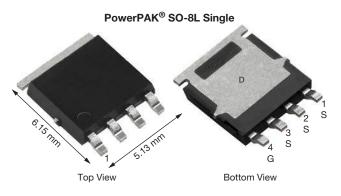
SQJ457EP



Vishay Siliconix

Automotive P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	-60
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 V$	0.0250
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.0350
I _D (A)	-36
Configuration	Single
Package	PowerPAK SO-8L

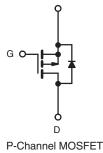


FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS COMPLIANT HALOGEN FREE



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ABSOLUTE MAXIMUM RATINGS (T _C =	25 °C, unles	s otherwise noted)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	-60	V
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current	T _C = 25 °C	1	-36	
	T _C = 125 °C	- I _D	-21	
Continuous Source Current (Diode Conduction) ^a		۱ _S	-60	А
Pulsed Drain Current ^b		I _{DM}	-100	
Single Pulse Avalanche Current		I _{AS}	-36	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	64.8	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	PD	68	W
	T _C = 125 °C	FD	22	vv
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C
Soldering Recommendations (Peak Temperature) ^{d, e}			260	0

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	68	°C/W
Junction-to-Case (Drain)		R _{thJC}	2.2	0/10

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR4 material).
- d. See solder profile (www.vishay.com/doc?73257). For PowerPAK SO-8L, the end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static					1		-
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0, I _D = -250 μΑ	-60	-	-	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = -250 μA	-1.5	-2.0	-2.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -60 V	-	-	-1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -60 V, T _J = 125 °C	-	-	-50	μA
		$V_{GS} = 0 V$	V _{DS} = -60 V, T _J = 175 °C	-	-	-150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \ge -5 V$	-30	-	-	Α
		$V_{GS} = -10 V$	I _D = -10 A	-	0.0210	0.0250	
Durin Country On Otata Desistance 3		V _{GS} = -10 V	I _D = -10 A, T _J = 125 °C	-	-	0.0409	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -10 A, T _J = 175 °C	-	-	0.0504	Ω
		V _{GS} = -4.5 V	I _D = -5 A	-	0.0288	0.0350	ĺ
Forward Transconductance b	9 _{fs}	V _{DS} =	-15 V, I _D = -10 A	-	26	-	S
Dynamic ^b		•			•		
Input Capacitance	C _{iss}			-	2600	3400	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = -25 V, f = 1 MHz	-	310	450	pF
Reverse Transfer Capacitance	C _{rss}			-	200	275	
Total Gate Charge ^c	Qg			-	65	100	
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = -10 V$	$V_{DS} = -30 \text{ V}, \text{ I}_{D} = -5 \text{ A}$	-	9.5	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	19	-	
Gate Resistance	Rg		f = 1 MHz	0.50	1.19	1.80	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	15	25	
Rise Time ^c	t _r	V _{DD}	= -30 V, R_{L} = 6 Ω	-	5	10	
Turn-Off Delay Time ^c	t _{d(off)}		$V_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	40	75	ns
Fall Time ^c	t _f			-	6	12	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	-100	A
Forward Voltage	V _{SD}	I	-10 A, V _{GS} = 0 V	_	-0.80	-1.2	V

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

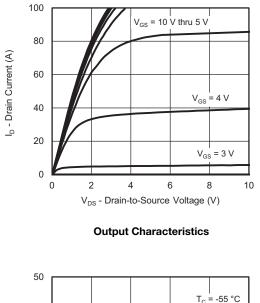
c. Independent of operating temperature.

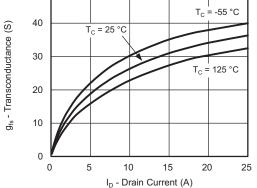
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

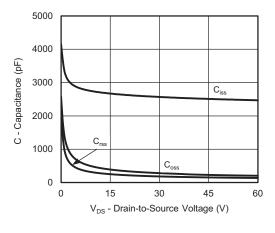


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

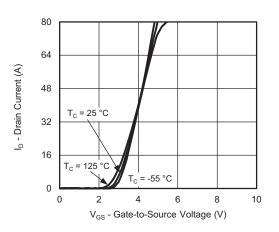




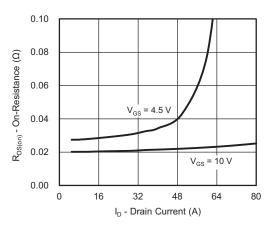
Transconductance



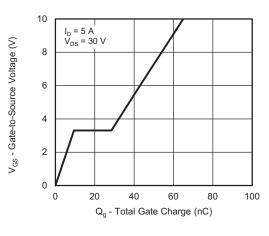
Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

3

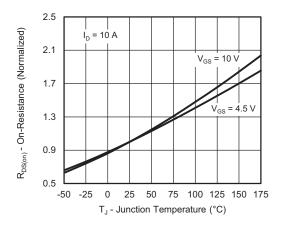
For technical questions, contact: <u>automostechsupport@vishay.com</u>
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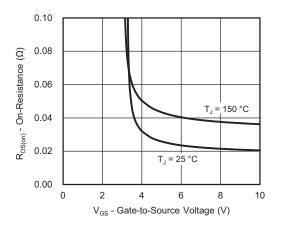
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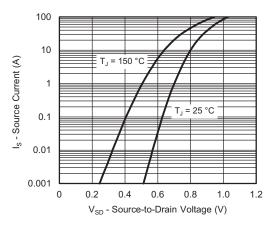
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



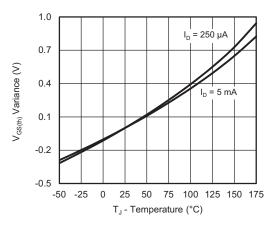
On-Resistance vs. Junction Temperature

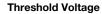


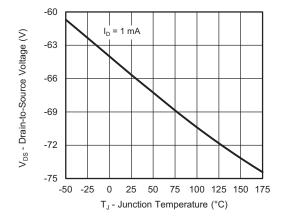
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



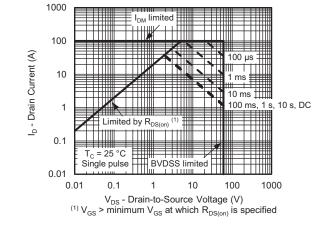




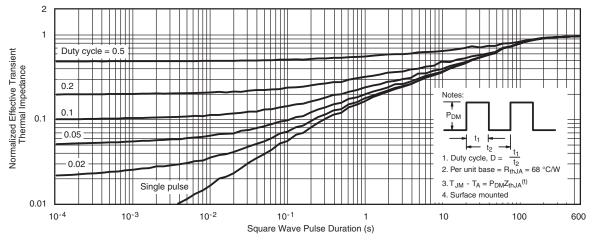
Drain-Source Breakdown vs. Junction Temperature



THERMAL RATINGS (T_C = 25 °C, unless otherwise noted)



Safe Operating Area



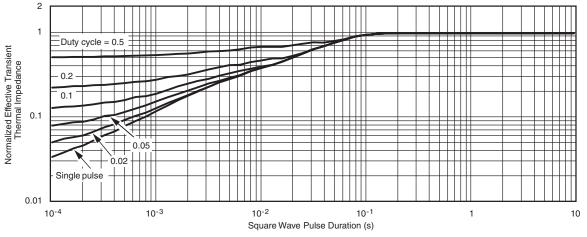
Normalized Thermal Transient Impedance, Junction-to-Ambient

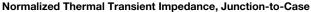


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THERMAL RATINGS ($T_C = 25 \text{ °C}$, unless otherwise noted)





Note

• The characteristics shown in the two graphs

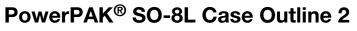
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

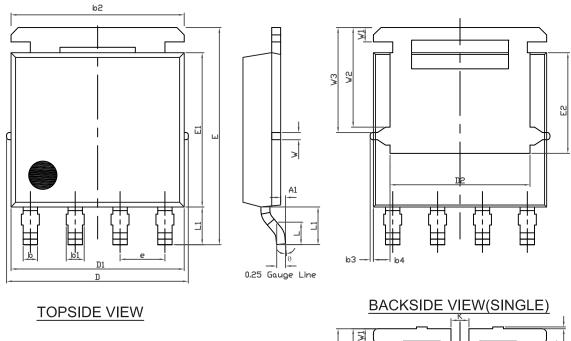
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

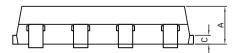
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

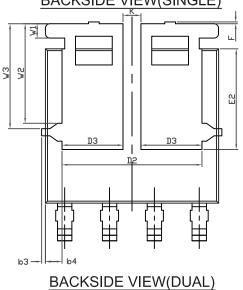
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Package Information



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DIM		MILLIMETERS			INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	MIN. NOM.		
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К		0.51			0.020		
W	0.23			0.009			
W1	0.41			0.016			
W2	2.82			0.111			
W3		2.96		0.117			
q	0°	-	10°	0°	-	10°	

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12

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